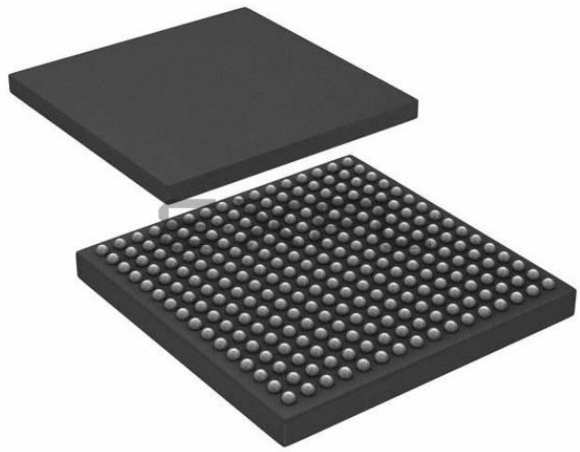

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	177
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-fgg256

User Nonvolatile FlashROM

ProASIC3 devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard ProASIC3 IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in the A3P015 and A3P030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The ProASIC3 development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

SRAM and FIFO

ProASIC3 devices (except the A3P015 and A3P030 devices) have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in A3P015 and A3P030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3 devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3 family contains six CCCs. One CCC (center west side) has a PLL. The A3P015 and A3P030 devices do not have a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

Table 2-2 • **Recommended Operating Conditions** [1]

Symbol	Parameters [1]		Commercial	Industrial	Units
T_J	Junction temperature		0 to 85[2]	-40 to 100[2]	°C
VCC[3]	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode	3.15 to 3.45	3.15 to 3.45	V
		Operation [4]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [5]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.3 V wide range DC supply voltage [6]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*
2. *Software Default Junction Temperature Range in the Libero® System-on-Chip (SoC) software is set to 0°C to +70°C for commercial, and -40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information regarding custom settings, refer to the New Project Dialog Box in the Libero SoC Online Help.*
3. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-18 on page 2-19.*
4. *VPUMP can be left floating during operation (not programming mode).*
5. *VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Table 2-13 • **Summary of I/O Output Buffer Power (Per Pin) – Default I/O Software Settings [1] Applicable to Standard I/O Banks**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW) [2]	Dynamic Power PAC10 (µW/MHz) [3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	431.08
3.3 V LVCMOS Wide Range[4]	35	3.3	–	431.08
2.5 V LVCMOS	35	2.5	–	247.36
1.8 V LVCMOS	35	1.8	–	128.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	89.46

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *P_{DC3} is the static power (where applicable) measured on VCCI.*
3. *P_{AC10} is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-19 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard Plus I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1] mA	IOH[1] mA
				Min V	Max V	Min V	Max V	Max V	Min V		
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.6	0.25 * VCCI	0.75 * VCCI	4	4
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-22 • Summary of AC Measuring Points

Standard	Measuring Trip Point (V_{trip})
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
3.3 V PCI	0.285 * VCCI (RR)
	0.615 * VCCI (FF)
3.3 V PCI-X	0.285 * VCCI (RR)
	0.615 * VCCI (FF)

Table 2-23 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-44 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	9.68	0.04	1.00	0.43	9.86	8.42	2.28	2.21	12.09	10.66	ns
	–1	0.56	8.23	0.04	0.85	0.36	8.39	7.17	1.94	1.88	10.29	9.07	ns
	–2	0.49	7.23	0.03	0.75	0.32	7.36	6.29	1.70	1.65	9.03	7.96	ns
4 mA	Std.	0.66	9.68	0.04	1.00	0.43	9.86	8.42	2.28	2.21	12.09	10.66	ns
	–1	0.56	8.23	0.04	0.85	0.36	8.39	7.17	1.94	1.88	10.29	9.07	ns
	–2	0.49	7.23	0.03	0.75	0.32	7.36	6.29	1.70	1.65	9.03	7.96	ns
6 mA	Std.	0.66	6.70	0.04	1.00	0.43	6.82	5.89	2.58	2.74	9.06	8.12	ns
	–1	0.56	5.70	0.04	0.85	0.36	5.80	5.01	2.20	2.33	7.71	6.91	ns
	–2	0.49	5.00	0.03	0.75	0.32	5.10	4.40	1.93	2.05	6.76	6.06	ns
8 mA	Std.	0.66	6.70	0.04	1.00	0.43	6.82	5.89	2.58	2.74	9.06	8.12	ns
	–1	0.56	5.70	0.04	0.85	0.36	5.80	5.01	2.20	2.33	7.71	6.91	ns
	–2	0.49	5.00	0.03	0.75	0.32	5.10	4.40	1.93	2.05	6.76	6.06	ns
12 mA	Std.	0.66	5.05	0.04	1.00	0.43	5.14	4.51	2.79	3.08	7.38	6.75	ns
	–1	0.56	4.29	0.04	0.85	0.36	4.37	3.84	2.38	2.62	6.28	5.74	ns
	–2	0.49	3.77	0.03	0.75	0.32	3.84	3.37	2.09	2.30	5.51	5.04	ns
16 mA	Std.	0.66	5.05	0.04	1.00	0.43	5.14	4.51	2.79	3.08	7.38	6.75	ns
	–1	0.56	4.29	0.04	0.85	0.36	4.37	3.84	2.38	2.62	6.28	5.74	ns
	–2	0.49	3.77	0.03	0.75	0.32	3.84	3.37	2.09	2.30	5.51	5.04	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-45 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	–1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	–2	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
4 mA	Std.	0.66	7.07	0.04	1.00	0.43	7.20	6.23	2.07	2.15	ns
	–1	0.56	6.01	0.04	0.85	0.36	6.12	5.30	1.76	1.83	ns
	–2	0.49	5.28	0.03	0.75	0.32	5.37	4.65	1.55	1.60	ns
6 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	–1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns
8 mA	Std.	0.66	4.41	0.04	1.00	0.43	4.49	3.75	2.39	2.69	ns
	–1	0.56	3.75	0.04	0.85	0.36	3.82	3.19	2.04	2.29	ns

3.3 V LVCMOS Wide Range

Table 2-47 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min V	Max V	Min V	Max V	Max V	Min V	µA	µA	Max mA[4]	Max mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	132	127	10	10
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	268	181	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 85°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*
6. *Software default selection highlighted in gray.*

Table 2-48 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min V	Max V	Min V	Max V	Max V	Min V	µA	µA	Max mA[4]	Max mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
4. *Currents are measured at 85°C junction temperature.*
5. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*
6. *Software default selection highlighted in gray.*

Table 2-62 • 2.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	–1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	–2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	–1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	–2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-63 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	–1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	–2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	–1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	–2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

Table 2-70 • **1.8 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.86	0.04	1.22	0.43	9.14	11.86	2.77	1.66	11.37	14.10	ns
	–1	0.56	10.09	0.04	1.04	0.36	7.77	10.09	2.36	1.41	9.67	11.99	ns
	–2	0.49	8.86	0.03	0.91	0.32	6.82	8.86	2.07	1.24	8.49	10.53	ns
4 mA	Std.	0.66	6.91	0.04	1.22	0.43	5.86	6.91	3.22	2.84	8.10	9.15	ns
	–1	0.56	5.88	0.04	1.04	0.36	4.99	5.88	2.74	2.41	6.89	7.78	ns
	–2	0.49	5.16	0.03	0.91	0.32	4.38	5.16	2.41	2.12	6.05	6.83	ns
6 mA	Std.	0.66	4.45	0.04	1.22	0.43	4.18	4.45	3.53	3.38	6.42	6.68	ns
	–1	0.56	3.78	0.04	1.04	0.36	3.56	3.78	3.00	2.88	5.46	5.69	ns
	–2	0.49	3.32	0.03	0.91	0.32	3.12	3.32	2.64	2.53	4.79	4.99	ns
8 mA	Std.	0.66	3.92	0.04	1.22	0.43	3.93	3.92	3.60	3.52	6.16	6.16	ns
	–1	0.56	3.34	0.04	1.04	0.36	3.34	3.34	3.06	3.00	5.24	5.24	ns
	–2	0.49	2.93	0.03	0.91	0.32	2.93	2.93	2.69	2.63	4.60	4.60	ns
12 mA	Std.	0.66	3.53	0.04	1.22	0.43	3.60	3.04	3.70	4.08	5.84	5.28	ns
	–1	0.56	3.01	0.04	1.04	0.36	3.06	2.59	3.15	3.47	4.96	4.49	ns
	–2	0.49	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
16 mA	Std.	0.66	3.53	0.04	1.22	0.43	3.60	3.04	3.70	4.08	5.84	5.28	ns
	–1	0.56	3.01	0.04	1.04	0.36	3.06	2.59	3.15	3.47	4.96	4.49	ns
	–2	0.49	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

***Table 2-100* • Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-111 • A3P250 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	0.80	1.01	0.91	1.15	1.07	1.36	ns
t_{RCKH}	Input High Delay for Global Clock	0.78	1.04	0.89	1.18	1.04	1.39	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-112 • A3P400 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	0.87	1.09	0.99	1.24	1.17	1.46	ns
t_{RCKH}	Input High Delay for Global Clock	0.86	1.11	0.98	1.27	1.15	1.49	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Embedded SRAM and FIFO Characteristics

SRAM

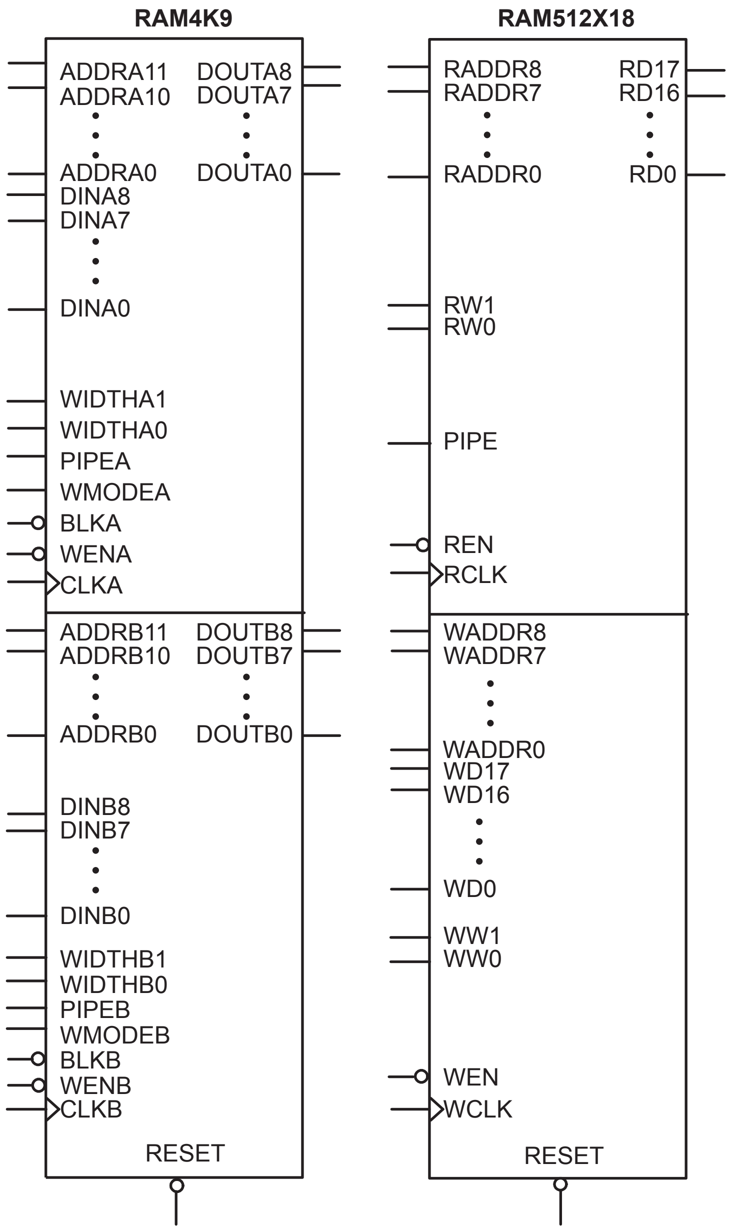

***Figure 2-30 •* RAM Models**

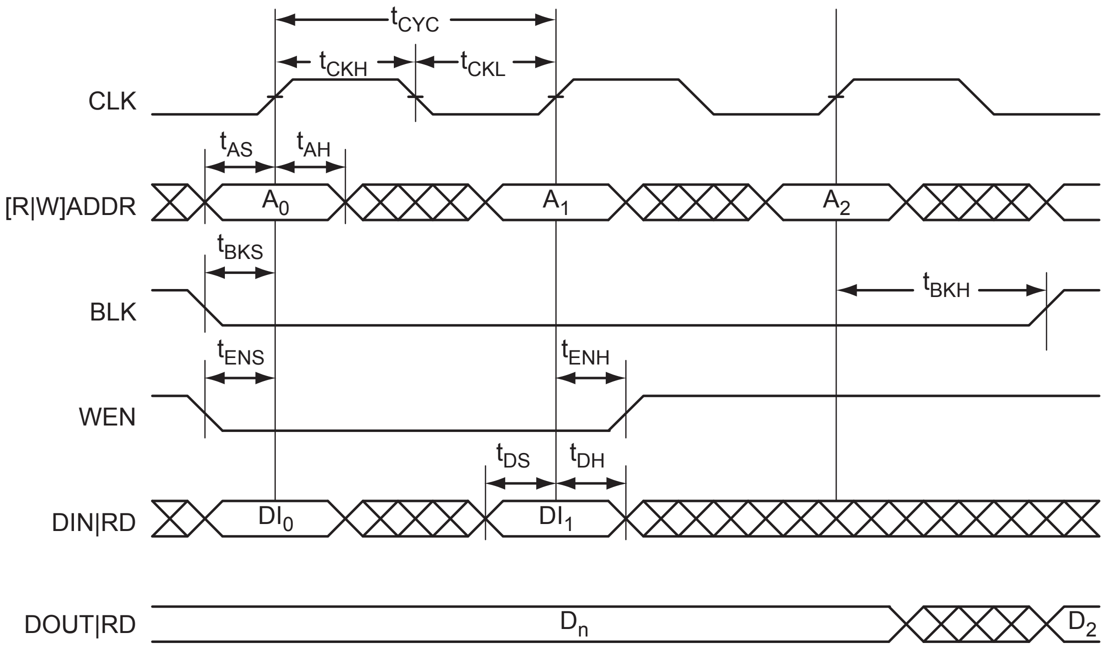

Figure 2-33 • **RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

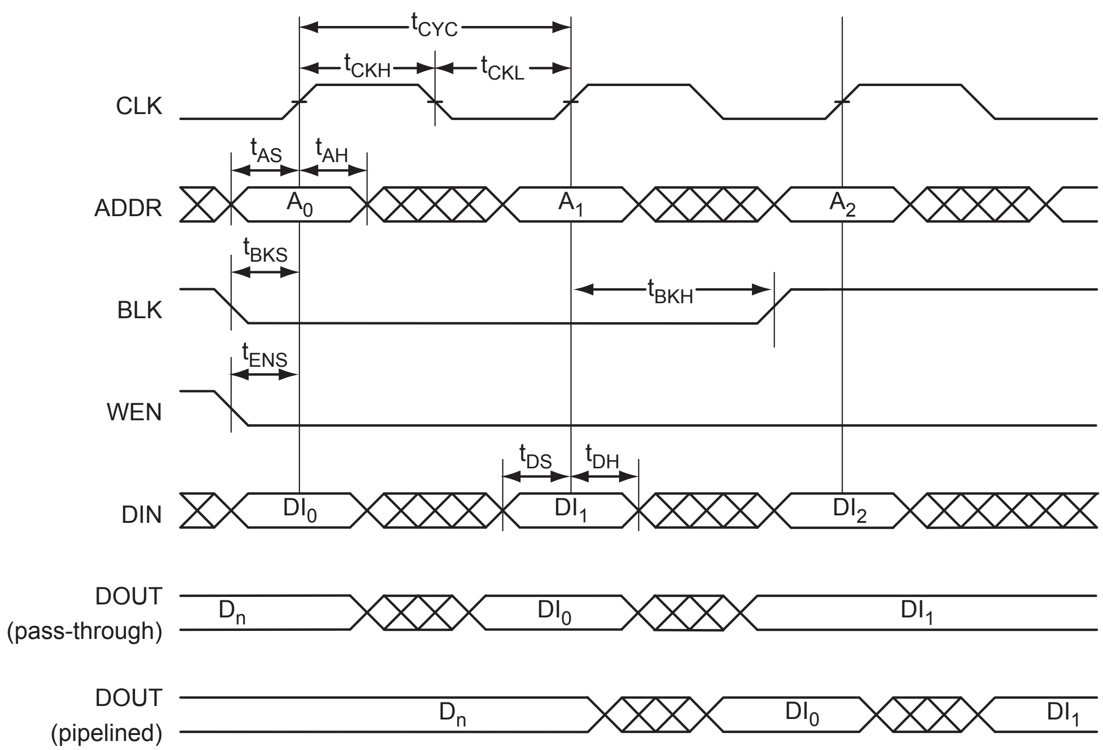

Figure 2-34 • **RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.**

FIFO

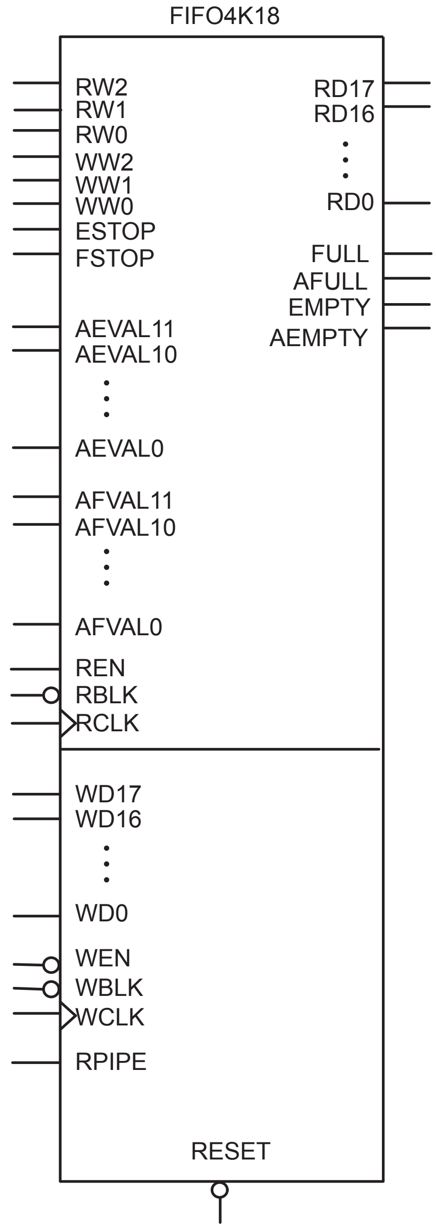

***Figure 2-36* • FIFO Model**

Table 2-122 • A3P250 FIFO 2k×2
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.39	5.00	5.88	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

Table 2-123 • A3P250 FIFO 4k×1
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.86	5.53	6.50	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns

VJTAG JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design.

If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP Programming Supply Voltage

ProASIC3 devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in Table 2-2 on page 2-2.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 µF and 0.33 µF capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to V_{CCI}. With V_{CCI}, VMV, and V_{CC} supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure section of the handbook for the device you are using for an explanation of the naming of global pins.

FF Flash*Freeze Mode Activation Pin

Flash*Freeze is available on IGLOO, ProASIC3L, and RT ProASIC3 devices. It is not supported on ProASIC3/E devices. The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active-low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O. For IGLOOe, ProASIC3EL, and RT ProASIC3 only, the FF pin can be configured as a Schmitt trigger input.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 1 for more information.

Table 1 • **Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance
3.3 V	200 Ω –1 kΩ
2.5 V	200 Ω –1 kΩ
1.8 V	500 Ω –1 kΩ
1.5 V	500 Ω –1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on the JTAG chain*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin is pulled down.*

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

The TRST pin functions as an active low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 1 and must satisfy the parallel resistance value requirement. The values in Table 1 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

PQ208	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC

PQ208	
Pin Number	A3P250 Function
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P250 Function
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

Revision	Changes	Page
Revision 5 (Aug 2008) DC and Switching Characteristics v1.3	TJ, Maximum Junction Temperature, was changed to 100° from 110º in the "Thermal Characteristics" section and EQ 1. The calculated result of Maximum Power Allowed has thus changed to 1.463 W from 1.951 W.	2-6
	Values for the A3P015 device were added to Table 2-7 • Quiescent Supply Current Characteristics.	2-7
	Values for the A3P015 device were added to Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices. P_{AC14} was removed. Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices is new.	2-11, 2-12
	The "PLL Contribution—PPLL" section was updated to change the P_{PLL} formula from $P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-14
	Both fall and rise values were included for $t_{DDRISUD}$ and t_{DDRIHD} in Table 2-102 • Input DDR Propagation Delays.	2-78
	Table 2-107 • A3P015 Global Resource is new.	2-86
	The typical value for Delay Increments in Programmable Delay Blocks was changed from 160 to 200 in Table 2-115 • ProASIC3 CCC/PLL Specification.	2-90
Revision 4 (Jun 2008) DC and Switching Characteristics v1.2	Table note references were added to Table 2-2 • Recommended Operating Conditions 1, and the order of the table notes was changed.	2-2
	The title for Table 2-4 • Overshoot and Undershoot Limits 1 was modified to remove "as measured on quiet I/Os." Table note 1 was revised to remove "estimated SSO density over cycles." Table note 2 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "Power per I/O Pin" section was updated to include 3 additional tables pertaining to input buffer power and output buffer power.	2-7
	Table 2-29 • I/O Output Buffer Maximum Resistances 1 was revised to include values for 3.3 V PCI/PCI-X.	2-27
	Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-66
Revision 3 (Jun 2008) Packaging v1.3	Pin numbers were added to the "QN68 – Bottom View" package diagram. Note 2 was added below the diagram.	4-3
	The "QN132 – Bottom View" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-6
Revision 2 (Feb 2008) Product Brief v1.0	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	This document was updated to include A3P015 device information. QN68 is a new package that was added because it is offered in the A3P015. The following sections were updated: "Features and Benefits" "ProASIC3 Ordering Information" "Temperature Grade Offerings" "ProASIC3 Flash Family FPGAs" "A3P015 and A3P030" note Introduction and Overview (NA)	N/A

Revision	Changes	Page
Revision 2 (cont'd)	The "ProASIC3 FPGAs Package Sizes Dimensions" table is new.	III
	In the "ProASIC3 Ordering Information", the QN package measurements were updated to include both 0.4 mm and 0.5 mm.	IV
	In the General Description section the number of I/Os was updated from 288 to 300.	1-1
Packaging v1.2	The "QN68 – Bottom View" section is new.	4-3
Revision 1 (Feb 2008) DC and Switching Characteristics v1.1	In Table 2-2 • Recommended Operating Conditions 1, T_J was listed in the symbol column and was incorrect. It was corrected and changed to T_A.	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-14
	In Table 2-21 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said T_J and it was corrected and changed to T_A.	2-21
	In Table 2-115 • ProASIC3 CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-90
	Table 2-125 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-108
Packaging v1.1	In the "VQ100" A3P030 pin table, the function of pin 63 was incorrect and changed from IO39RSB0 to GDB0/IO38RSB0.	4-19
Revision 0 (Jan 2008)	This document was previously in datasheet v2.2. As a result of moving to the handbook format, Actel has restarted the version numbers.	N/A
v2.2 (July 2007)	The M7 and M1 device part numbers have been updated in Table 1 • ProASIC3 Product Family, "I/Os Per Package", "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix".	i, ii, iii, iii, iv
	The words "ambient temperature" were added to the temperature range in the "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A, ambient temperature, and table notes 4–6 were added.	3-2
v2.1 (May 2007)	In the "Clock Conditioning Circuit (CCC) and PLL" section, the Wide Input Frequency Range (1.5 MHz to 200 MHz) was changed to (1.5 MHz to 350 MHz).	i
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	i
	In the "I/Os Per Package" section, the A3P030, A3P060, A3P125, ACP250, and A3P600 device I/Os were updated.	ii
	Table 3-5 • Package Thermal Resistivities was updated with A3P1000 information. The note below the table is also new.	3-5